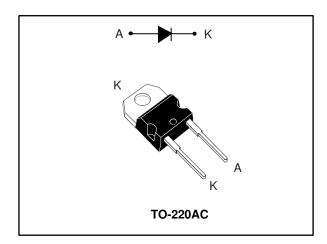


STPSC15H12-Y

Automotive grade 1200 V power Schottky silicon carbide diode

Datasheet - production data



Features



- No or negligible reverse recovery
- Switching behavior independent of temperature
- Robust high voltage periphery
- PPAP capable
- Operating T_i from -40 °C to 175 °C

Description

The SiC diode, available in TO-220AC, is an ultrahigh performance power Schottky rectifier. It is manufactured using a silicon carbide substrate. The wide band-gap material allows the design of a low V_F Schottky diode structure with a 1200 V rating. Due to the Schottky construction, no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature. Especially suited for use in PFC and secondary side applications, this ST SiC diode will boost the performance in hard switching conditions. This rectifier will enhance the performance of the targeted application. Its high forward surge capability ensures a good robustness during transient phases.

Table 1: Device summary

Symbol	Value
$I_{F(AV)}$	15 A
V_{RRM}	1200 V
T _j (max.)	175 °C
V _F (typ.)	1.35 V

Characteristics STPSC15H12-Y

1 Characteristics

Table 2: Absolute ratings (limiting values at 25 °C, unless otherwise specified)

Symbol		Value	Unit		
V _{RRM}	Repetitive peak reverse voltage (T _j = -40 °C to +175 °C)			1200	V
I _{F(RMS)}	Forward rms current			38	Α
I _{F(AV)}	Average forward current	T _C = 155 °C, DC currer	nt	15	Α
I _{FRM}	Repetitive peak forward current	T _C = 155 °C, T _j = 175 °C, δ = 0.1		58	Α
Surge non repetitive forward current		t 10 ma simussidal	T _C = 25 °C	105	
		$t_p = 10 \text{ ms sinusoidal}$	T _C = 150 °C	90	Α
	Torward darront	$t_p = 10 \ \mu s \ square$ $T_C = 25 \ ^{\circ}C$		630	
T _{stg}	Storage temperature range			-65 to +175	°C
Tj	Operating junction temperature			-40 to +175	°C

Table 3: Thermal parameters

Symbol	Parameter	Typ. value	Max. value	Unit
R _{th(j-c)}	Junction to case	0.45	0.6	°C/W

Table 4: Static electrical characteristics

Symbo	Parameter	Test conditions		Min.	Тур.	Max.	Unit
1 (1)	L (1)			-	7.5	90	
I _R ⁽¹⁾	Reverse leakage current	T _j = 150 °C	$V_R = V_{RRM}$	-	45	600	μΑ
V _F (2)	Forward voltage drop	T _j = 25 °C	I_ 1E A	-	1.35	1.50	V
VF(2)		T _j = 150 °C	I _F = 15 A	-	1.75	2.25	V

Notes:

 $^{(1)}$ Pulse test: tp = 10 ms, δ < 2%

(2) Pulse test: t_p = 500 μs, δ < 2%

To evaluate the conduction losses use, the following equation:

 $P = 1.09 \ x \ I_{F(AV)} + 0.0775 \ x \ I_{F^2(RMS)}$

Table 5: Dynamic electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
Qcj ⁽¹⁾	Total capacitive charge	V _R = 800 V	-	94	1	nC
C	Total conscitores	$V_R = 0 \text{ V}, T_c = 25 \text{ °C}, F = 1 \text{ MHz}$	-	1200	-	,, F
Cj	Total capacitance	V _R = 800 V, T _c = 25 °C, F = 1 MHz	-	78	-	pF

Notes:

⁽¹⁾Most accurate value for the capacitive charge: $Q_{cj}(V_R) = \int_0^{V_R} C_j(V) dV$



STPSC15H12-Y Characteristics

1.1 Characteristics (curves)

1.0

Figure 1: Forward voltage drop versus forward current (typical values)

1.5

Figure 2: Reverse leakage current versus reverse voltage applied (typical values)

1.E+02

1.E+01

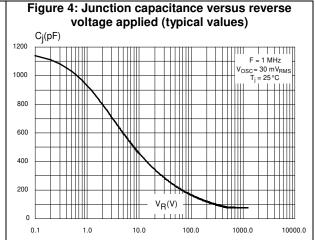
1.E+01

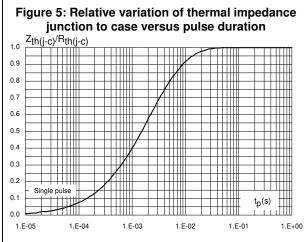
1.E-02

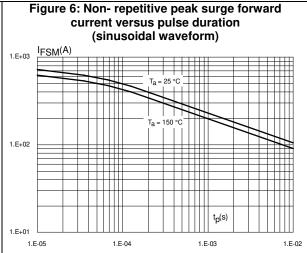
1.E-03

0 100 200 300 400 500 600 700 800 900 1000 1100 1200

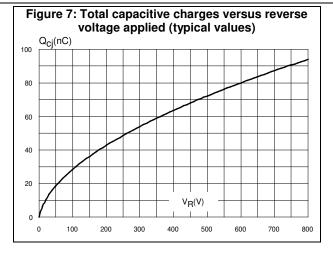
Figure 3: Peak forward current versus case temperature I_M(A) 140 $\delta = 0.1$ 120 δ= tp/T + 80 $\delta = 0.3$ 60 $\delta = 0.5$ 40 20 $T_{c}(^{\circ}C)$ 0 0 25 50 75 100 125 150







Characteristics STPSC15H12-Y



STPSC15H12-Y Package information

2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK® is an ST trademark.

• Cooling method: by conduction (C)

• Epoxy meets UL 94,V0

Recommended torque value: 0.55 N·m

• Maximum torque value: 0.7 N·m

2.1 TO-220AC package information

Figure 8: TO-220AC package outline

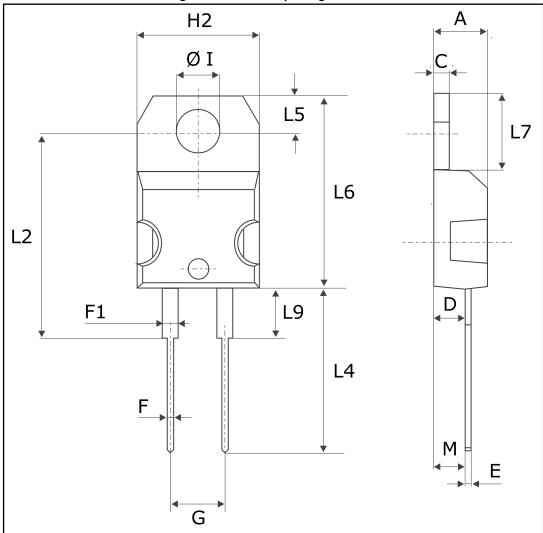


Table 6: TO-220AC package mechanical data

Table 0. 10-220A0 package mechanical data						
		Dimer	ensions			
Ref.	Millim	neters	Inches			
	Min.	Max.	Min.	Max.		
Α	4.40	4.60	0.173	0.181		
С	1.23	1.32	0.048	0.051		
D	2.40	2.72	0.094	0.107		
E	0.49	0.70	0.019	0.027		
F	0.61	0.88	0.024	0.034		
F1	1.14	1.70	0.044	0.066		
G	4.95	5.15	0.194	0.202		
H2	10.00	10.40	0.393	0.409		
L2	16.40	16.40 typ.		5 typ.		
L4	13.00	14.00	0.511	0.551		
L5	2.65	2.95	0.104	0.116		
L6	15.25	15.75	0.600	0.620		
L7	6.20	6.60	0.244	0.259		
L9	3.50	3.93	0.137	0.154		
М	2.6 typ.		0.102	2 typ.		
Diam	3.75	3.85	0.147	0.151		

STPSC15H12-Y Ordering information

3 Ordering information

Table 7: Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPSC15H12DY	STPSC15H12DY	TO-220AC	1.86 g	50	Tube

4 Revision history

Table 8: Document revision history

Date	Revision	Changes
05-Jan-2017	1	First issue

IMPORTANT NOTICE - PLEASE READ CAREFULLY

STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST's terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers' products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2017 STMicroelectronics - All rights reserved

